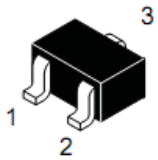
WPM2026

Single P-Channel, -20V, -3.2A, Power MOSFET

Http://www.sh-willsemi.com

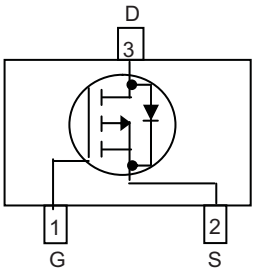
V_{DS} (V)	Rds(on) (Ω)
-20	0.056@ V_{GS}= – 4.5V
	0.069@ V_{GS}= – 2.5V
	0.086@ V_{GS}= – 1.8V



SOT-23

Descriptions

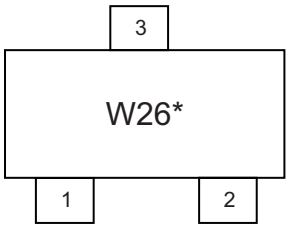
The WPM2026 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS\ (ON)}$ with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WPM2026 is Pb-free and Halogen-free.



Pin configuration (Top view)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package SOT-23



W26= Device Code

* = Month (A~Z)

Marking

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Order information

Device	Package	Shipping
WPM2026-3/TR	SOT-23	3000/Reel&Tape

Absolute Maximum ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	-20		V
Gate-Source Voltage		V_{GS}	±12		
Continuous Drain Current [a]	T_A=25°C	I_D	-3.2	-2.9	A
	T_A=70°C		-2.6	-2.3	
Maximum Power Dissipation [a]	T_A=25°C	P_D	0.9	0.8	W
	T_A=70°C		0.6	0.5	
Continuous Drain Current [b]	T_A=25°C	I_D	-2.9	-2.7	A
	T_A=70°C		-2.3	-2.1	
Maximum Power Dissipation [b]	T_A=25°C	P_D	0.7	0.6	W
	T_A=70°C		0.5	0.4	
Pulsed Drain Current [c]		I_{DM}	-12		A
Operating Junction Temperature		T_J	150		°C
Lead Temperature		T_L	260		°C
Storage Temperature Range		T_{stg}	-55 to 150		°C

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance [a]	t ≤ 10 s	$R_{\theta JA}$	105	130	°C/W
	Steady State		120	155	
Junction-to-Ambient Thermal Resistance [b]	t ≤ 10 s	$R_{\theta JA}$	130	160	
	Steady State		145	190	
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	40	60	

a Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

b Surface mounted on FR4 board using minimum pad size, 1oz copper

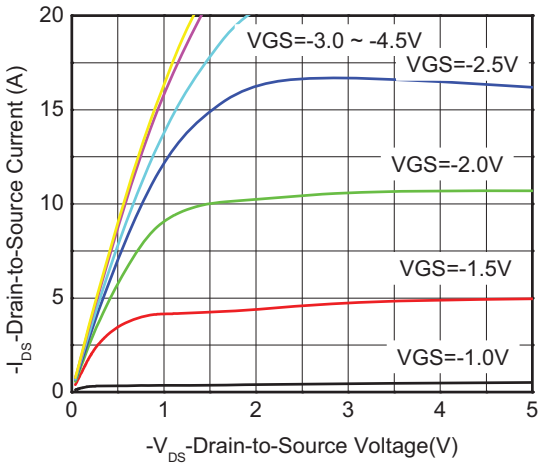
c Repetitive rating, pulse width limited by junction temperature, t_p=10μs, Duty Cycle=1%

d Repetitive rating, pulse width limited by junction temperature T_J=150°C.

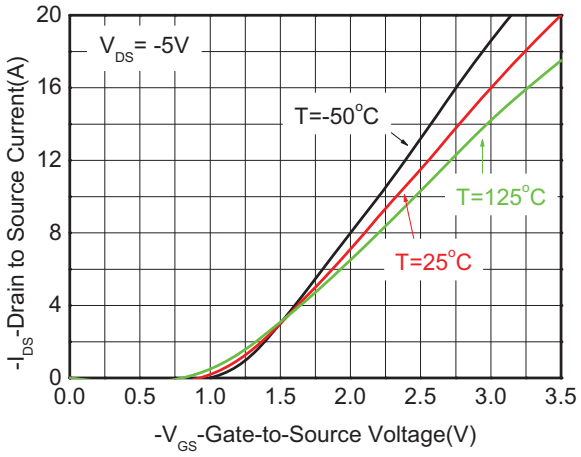
Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0 V, I_D = -250uA	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-16 V, V_{GS} = 0V			-1	uA
Gate-to-source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±12V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = -250uA	-0.35	-0.6	-1.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	V_{GS} = -4.5V, I_D = -3.2A		56	65	mΩ
		V_{GS} = -2.5V, I_D = -2.8A		69	81	
		V_{GS} = -1.8V, I_D = -2.3A		86	110	
Forward Transconductance	g_{FS}	V_{DS} = -5 V, I_D = -3.6A		10		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = -10 V		1130		pF
Output Capacitance	C_{OSS}			120		
Reverse Transfer Capacitance	C_{RSS}			115		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = -4.5 V, V_{DS} = -10 V, I_D = -2.7A		11		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.6		
Gate-to-Source Charge	Q_{GS}			1.3		
Gate-to-Drain Charge	Q_{GD}			2.7		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V_{GS} = -4.5 V, V_{DD} = -10 V, R_L=3.5 Ω, R_G=6 Ω		16		ns
Rise Time	tr			20		
Turn-Off Delay Time	td(OFF)			65		
Fall Time	tf			15		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = -1.0A		-0.62	-1.5	V

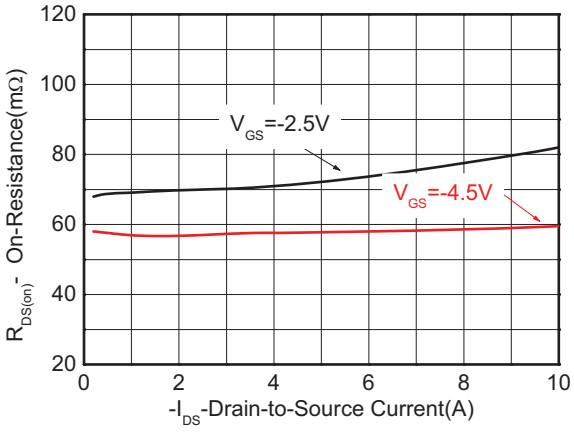
Typical Characteristics (Ta=25°C, unless otherwise noted)



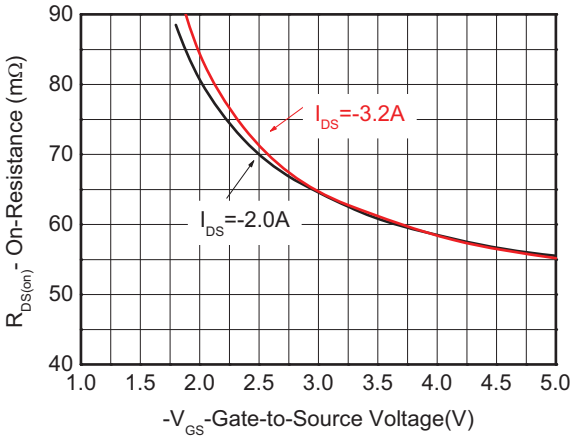
Output characteristics



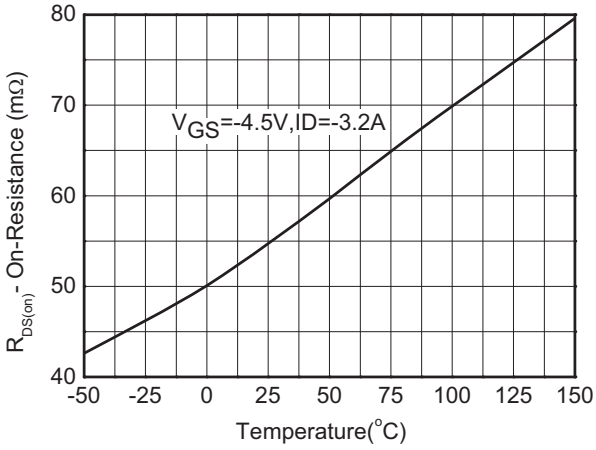
Transfer characteristics



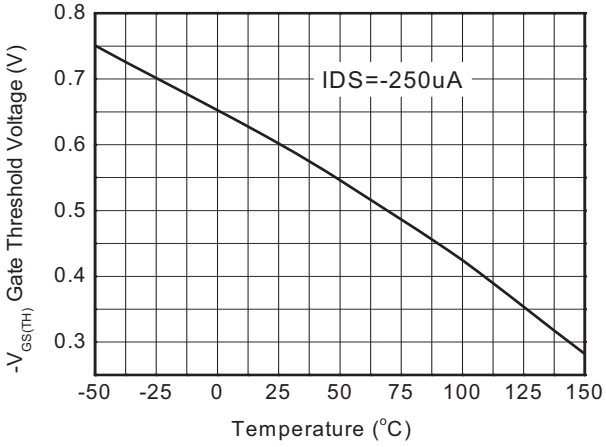
On-Resistance vs. Drain current



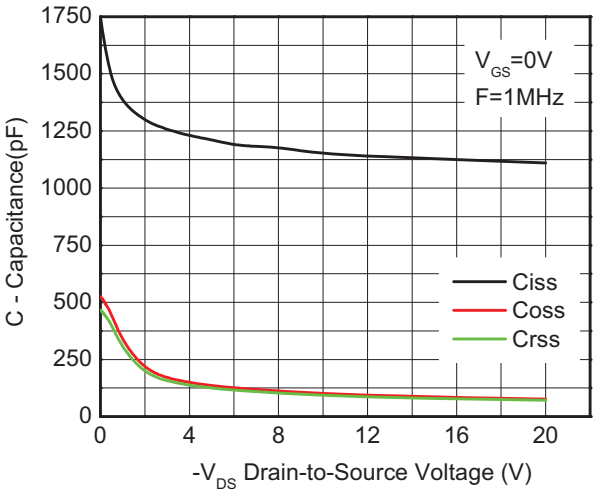
On-Resistance vs. Gate-to-Source voltage



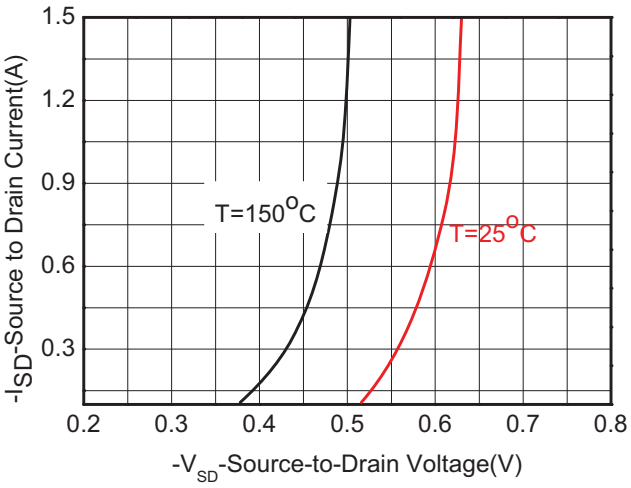
On-Resistance vs. Junction temperature



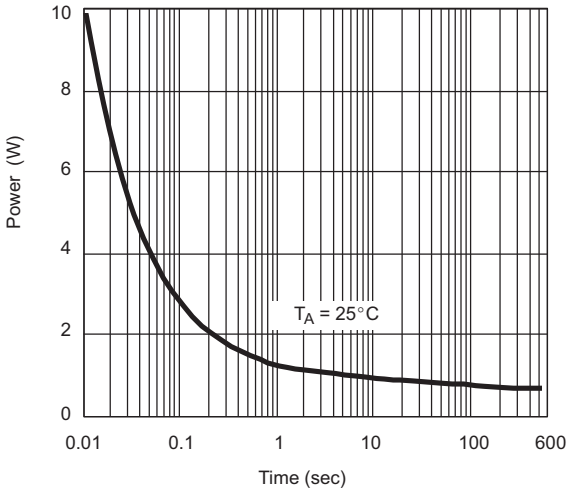
Threshold voltage vs. Temperature



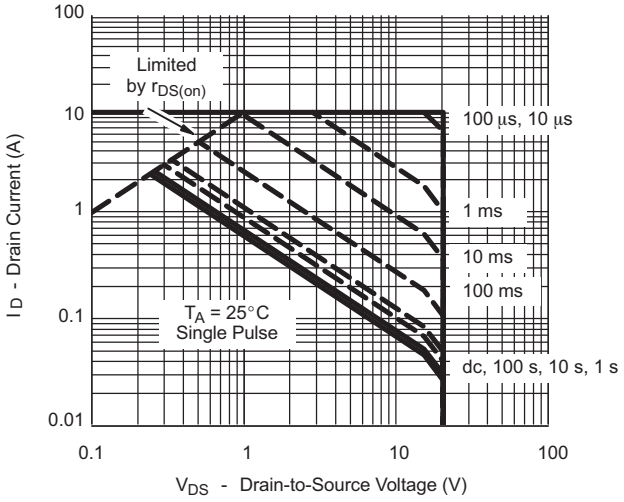
Capacitance



Body diode forward voltage



Single pulse power

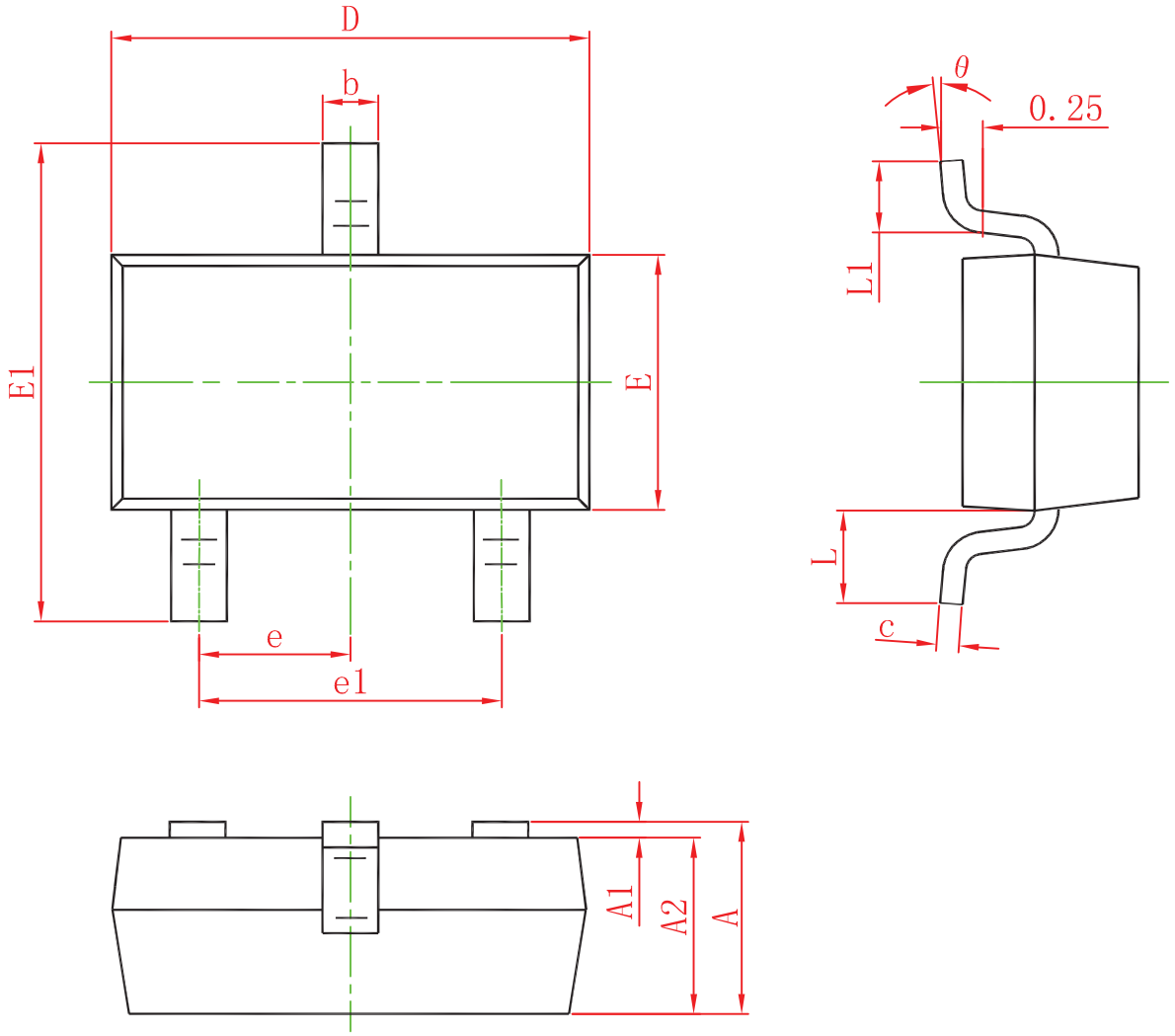


Safe operating area

Transient thermal response (Junction-to-Ambient)

Package outline dimensions

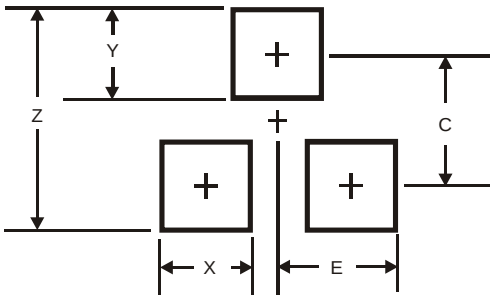
SOT-23



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.025	1.150
A1	0.000	0.050	0.100
A2	0.900	0.975	1.050
b	0.300	0.400	0.500
c	0.080	0.115	0.150
D	2.800	2.900	3.000
E	1.200	1.300	1.400
E1	2.250	2.400	2.550
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.550REF		
L1	0.300		0.500
θ	0°		8°

Suggested Land Pattern

SOT-23



Dimensions	SOT-23(mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35